General Description

FSMOS® MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially designed to use in motor control systems with driving voltage of more than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

RoHS compliant

Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switching mode power supply

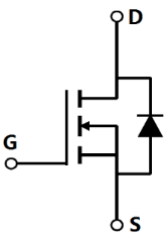
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$I_{D, pulse}$	320	A
$R_{DS(ON), max}$ @ V_{GS}=10V	11	mΩ
Q_g	30	nC

Marking Information

Product Name	Package	Marking
SFS15R11DNF	TO-252-2L	SFS15R11DN

Package & Pin information



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Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	150	V
Gate-source voltage	V_{GS}	±20	V
Continuous drain current[1], T_C=25 °C	I_D	80	A
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	320	A
Continuous diode forward current[1], T_C=25 °C	I_S	80	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	320	A
Power dissipation[3], T_C=25 °C	P_D	170	W
Single pulsed avalanche energy[5]	E_{AS}	280	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.87	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	150			V	V_{GS}=0 V, I_D=250 μA
Gate threshold voltage	$V_{GS(th)}$	3		4.5	V	V_{DS}=V_{GS}, I_D=250 μA
Drain-source on-state resistance	$R_{DS(ON)}$		9.6	11	mΩ	V_{GS}=10 V, I_D=30 A
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=20 V
				-100		V_{GS}=-20 V
Drain-source leakage current	I_{DSS}			1	μA	V_{DS}=150 V, V_{GS}=0 V
Gate resistance	R_G		1.6		Ω	f=1 MHz, Open drain

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Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1949		pF	V_{GS}=0 V, V_{DS}=75 V, f=100 kHz
Output capacitance	C_{oss}		719		pF	
Reverse transfer capacitance	C_{rss}		14		pF	
Turn-on delay time	$t_{d(on)}$		15		ns	V_{GS}=10 V, V_{DS}=80 V, R_G=2 Ω, I_D=40 A
Rise time	t_r		9		ns	
Turn-off delay time	$t_{d(off)}$		21		ns	
Fall time	t_f		9		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		30		nC	V_{GS}=10 V, V_{DS}=80 V, I_D=40 A
Gate-source charge	Q_{gs}		10		nC	
Gate-drain charge	Q_{gd}		10		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.1	V	I_S=30 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		88		ns	V_R=80 V, I_S=40 A, di/dt=100 A/μs
Reverse recovery charge	Q_{rr}		72		nC	
Peak reverse recovery current	I_{rrm}		1.6		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=100V,V_{GS}=10 V, L=0.3 mH, starting T_j=25 °C.

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Electrical Characteristics Diagrams

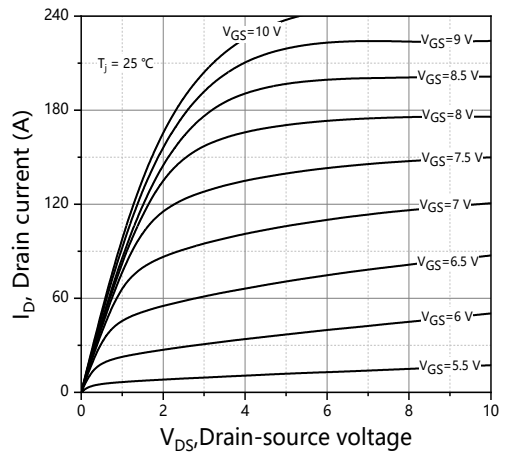

Figure 1. Typ. output characteristics

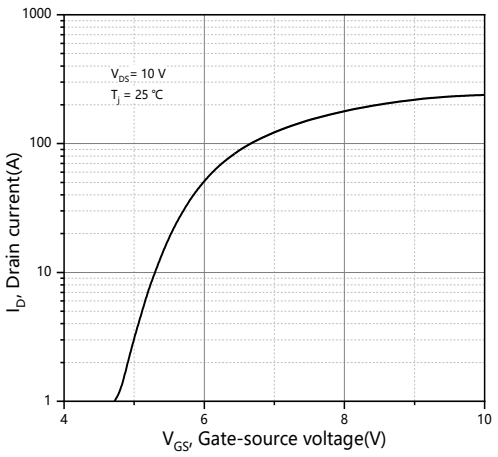

Figure 2. Typ. transfer characteristics

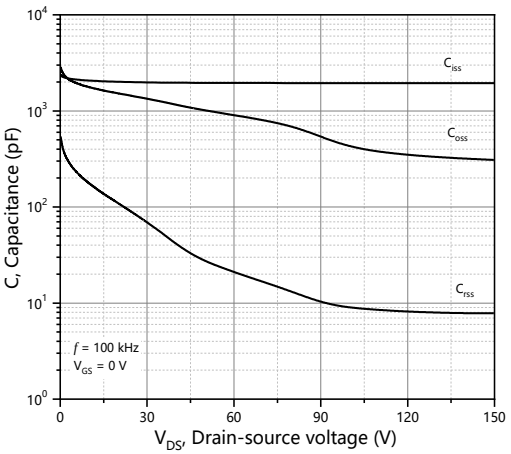

Figure 3. Typ. capacitances

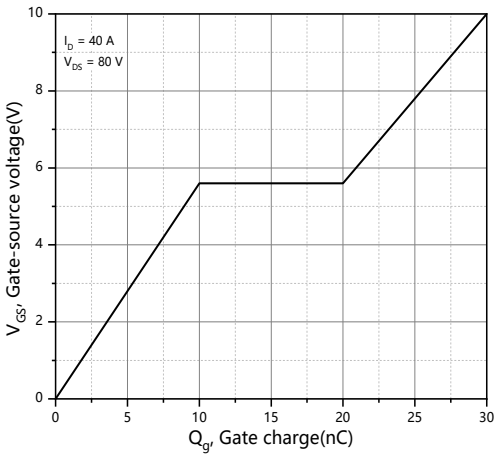

Figure 4. Typ. gate charge

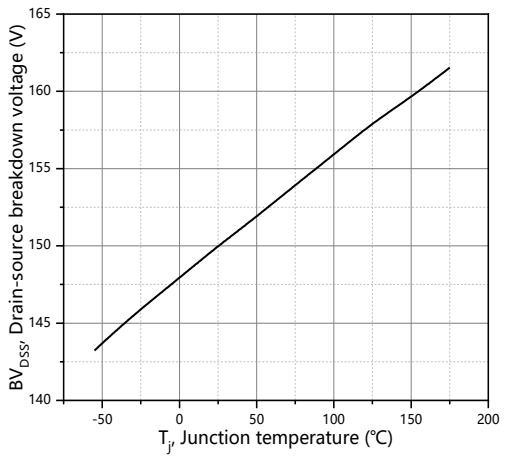

Figure 5. Drain-source breakdown voltage

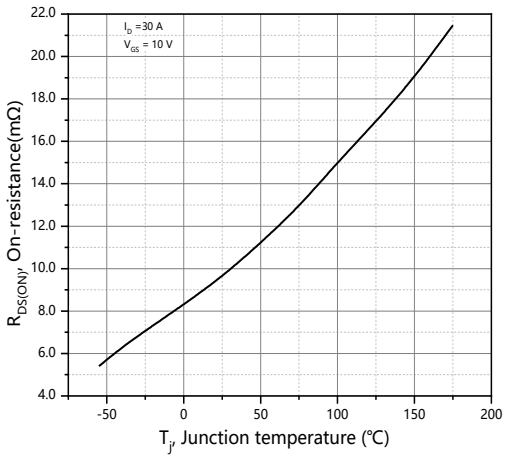

Figure 6. Drain-source on-state resistance

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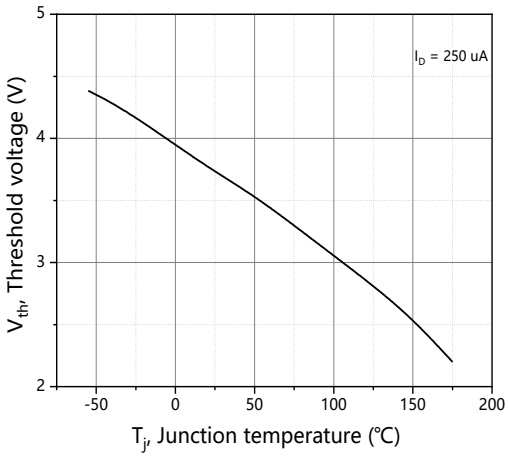

Figure 7. Threshold voltage

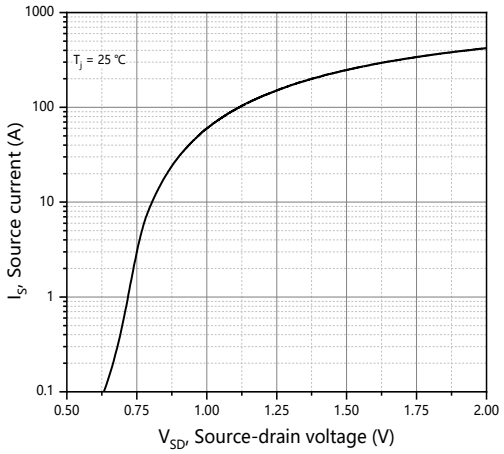

Figure 8. Forward characteristic of body diode

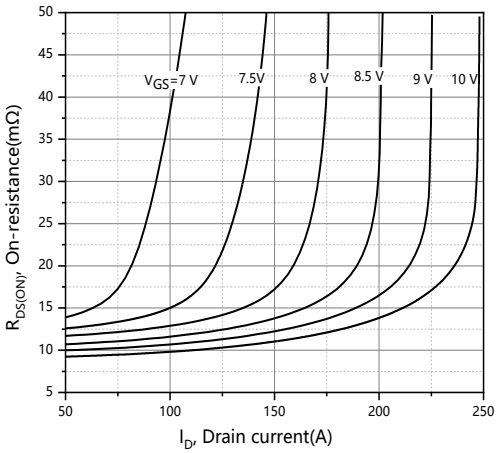

Figure 9. Drain-source on-state resistance

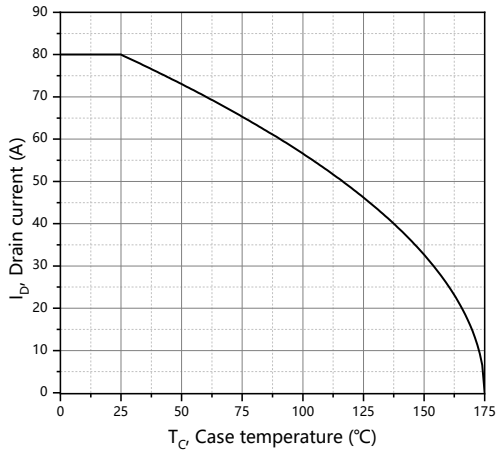

Figure 10. Drain current

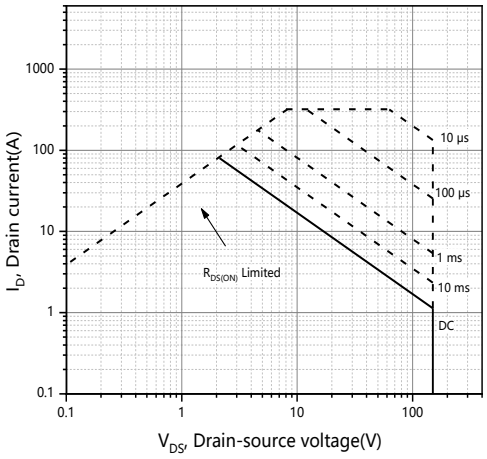

Figure 11. Safe operation area T_C=25℃

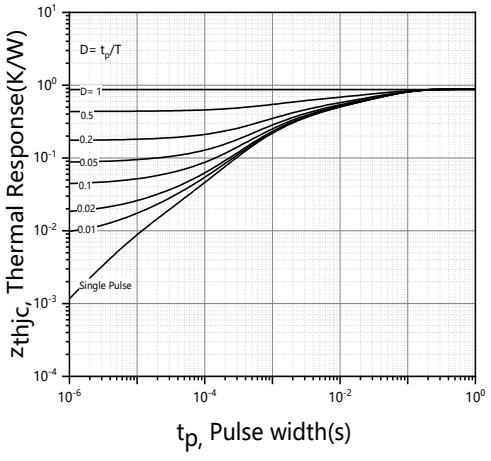

Figure 12. Max. transient thermal impedance

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Test circuits and waveforms

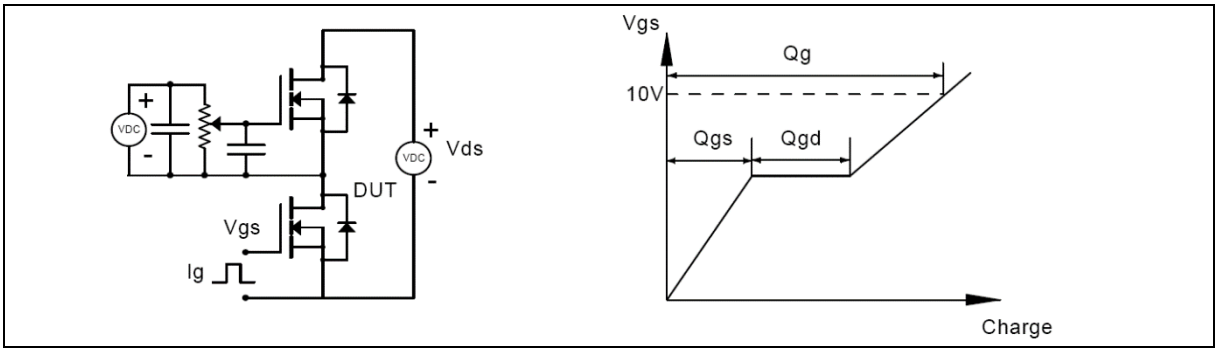


Figure 1. Gate charge test circuit & waveform

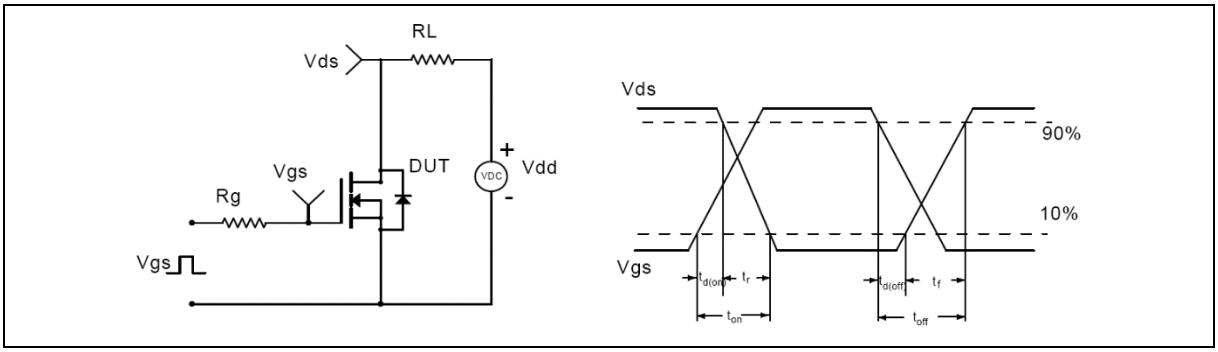


Figure 2. Switching time test circuit & waveforms

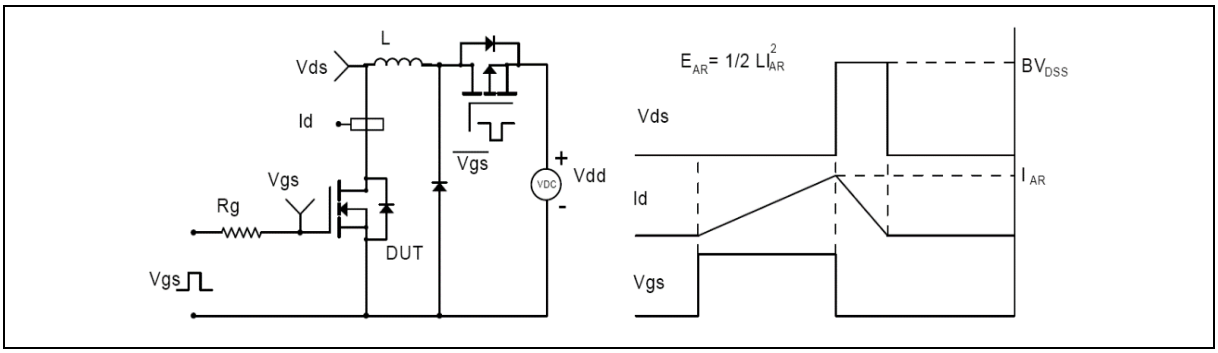


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

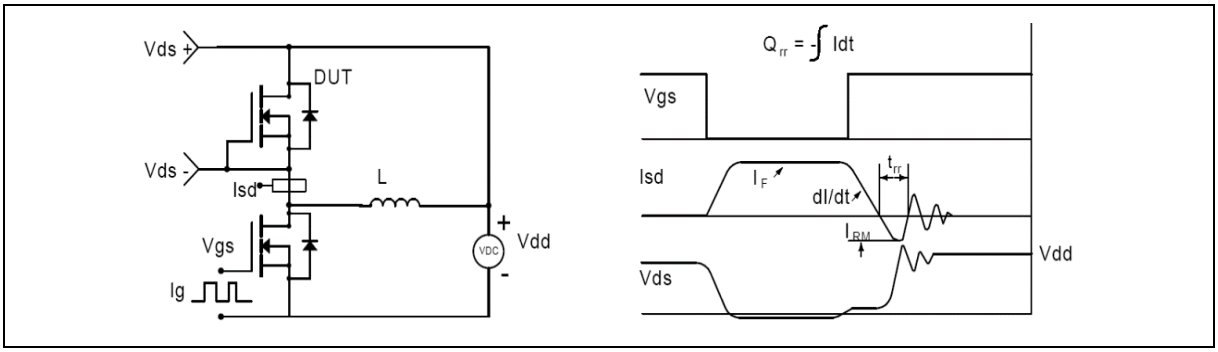
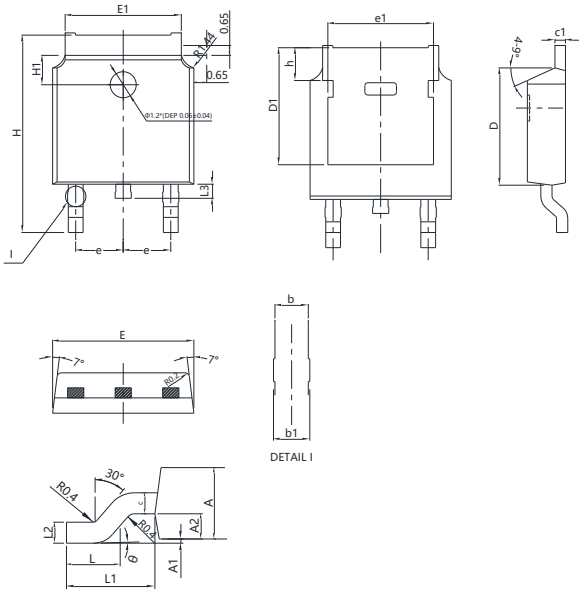


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	2.2	2.3	2.4
A1	0.00	0.075	0.15
A2	0.97	1.02	1.07
b	0.60	0.67	0.74
b1	0.65	-	1.15
c	0.508	0.528	0.548
c1	0.478	0.508	0.538
D	6.0	6.1	6.2
D1	5.15	5.25	5.35
E	6.5	6.6	6.7
E1	5.184	5.334	5.484
e	2.286BSC		
e1	4.806	4.826	4.846
H	9.8	10.0	10.2
H1	1.5	1.6	1.7
h	1.15	1.25	1.35
L	1.4	1.5	1.6
L1	2.888 REF		
L2	0.51BSC		
L3	0.80	0.90	1.00
θ	0°	-	10°

Version ： TO-252-2L-G package outline dimension

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Ordering Information

Package Type	Units/ Reel	Reels / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO-252-2L-G	2500	2	5000	6	30000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFS15R11DNF	TO-252-2L	yes	yes	yes

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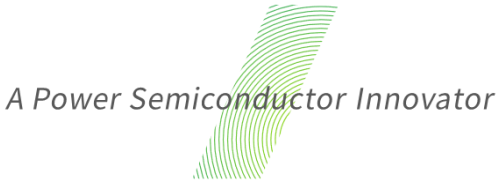
Revision History

Version	Revision History	Date
V1.0	Initial release	2025-03-05



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